

50W 808nm Infrared Laser Diode Bare Chip

Feature:

High reliability

Advanced in power,brightness,efficiency and divergence.

Customized Option if needed.

Data Sheet

Item No:LC808SB50

Item Name:50W 808nm Infrared Laser Diode Bare Chip

Operation

Center Wavelength	808nm
Output Power	50W
Operation Mode	CW
Power modulation	100%

Geometrical

Numbers of Emitters	19
Emitter width	150um
Cavity length	1000um
Emitter Pitch	500um
Filling factor	30%
Bar width	10000um

Electro Optical Data

Threshold current	6A
Operating current	48.5~50.5A
Operating voltage	1.8-2.0V
Slope efficiency	1.15W/A
Slow axis divergence	12
Fast axis divergence	39
Spectral width	4nm
Temperature characteristics	0.28nm/°C
Polarization	TE
LD operating temperature	25°C

808nm 50W LIV Curve

